

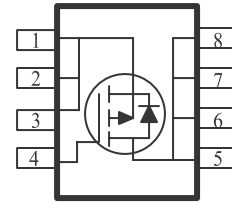
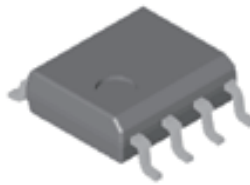
P-Channel 60-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize High Cell Density process. Low $r_{DS(on)}$ assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

- Low $r_{DS(on)}$ Provides Higher Efficiency and Extends Battery Life
- Miniature SO-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Extended VGS range (± 25) for battery pack applications

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ m(Ω)	I_D (A)
-60	17 @ $V_{GS} = -10V$	-9.3
	23 @ $V_{GS} = -4.5V$	-8.0



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ^a	$T_A = 25^\circ\text{C}$	I_D	± 9.3	A
	$T_A = 70^\circ\text{C}$		± 8.0	
Pulsed Drain Current ^b		I_{DM}	± 30	
Continuous Source Current (Diode Conduction) ^a		I_S	-2.5	A
Power Dissipation ^a	$T_A = 25^\circ\text{C}$	P_D	3.1	W
	$T_A = 70^\circ\text{C}$		2.0	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient ^a	$t \leq 10 \text{ sec}$	$R_{\theta JA}$	50	$^\circ\text{C/W}$

Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

SPECIFICATIONS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

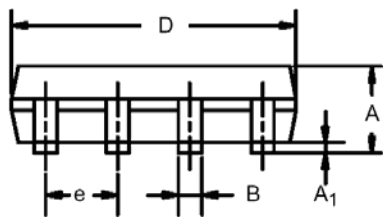
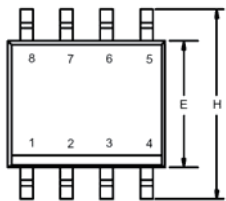
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 uA	-1			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -48 V, V _{GS} = 0 V			-1	uA
		V _{DS} = -48 V, V _{GS} = 0 V, T _J = 55°C			-10	
On-State Drain Current ^A	I _{D(on)}	V _{DS} = -5 V, V _{GS} = -10 V	-20			A
Drain-Source On-Resistance ^A	r _{DS(on)}	V _{GS} = -10 V, I _D = -9.3 A			17	mΩ
		V _{GS} = -4.5 V, I _D = -8.0 A			23	
Forward Tranconductance ^A	g _{fs}	V _{DS} = -15 V, I _D = -9.3 A		8		S
Diode Forward Voltage	V _{SD}	I _S = -2.5 A, V _{GS} = 0 V			-1.2	V
Dynamic ^b						
Total Gate Charge	Q _g	V _{DS} = -30 V, V _{GS} = -4.5 V, I _D = -8.0 A		46		nC
Gate-Source Charge	Q _{gs}			18		
Gate-Drain Charge	Q _{gd}			41		
Turn-On Delay Time	t _{d(on)}	V _{DD} = -30 V, R _L = 30 Ω , I _D = -1 A, V _{GEN} = -10 V, R _G = 6Ω		20		nS
Rise Time	t _r			20		
Turn-Off Delay Time	t _{d(off)}			205		
Fall-Time	t _f			90		

Notes

- Pulse test: $PW \leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

Package Information

SO-8: 8LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

